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# 20V Dual N-Channel MOSFET w/ESD Protected

#### TSSOP-8

#### Pin Definition:

# 8

1. Drain 1 8. Drain 2 2. Source 1 7. Source 2 3. Source 1 6. Source 2

4. Gate 1 5. Gate 2

## **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
20	22 @ V <sub>GS</sub> = 4.5V	6.5
	29 @ V <sub>GS</sub> = 2.5V	5.5

## **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance
- ESD Protect 2KV

## **Application**

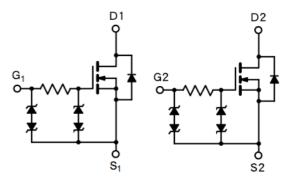
- Specially Designed for Li-on Battery Packs
- Battery Switch Application

## **Ordering Information**

Part No.	Package	Packing
TSM6968SDCA RVG	TSSOP-8	3Kpcs / 13" Reel

Note: "G" denotes for Halogen Free

## **Block Diagram**



**Dual N-Channel MOSFET** 

## Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Prain-Source Voltage		$V_{DS}$	20	V	
Gate-Source Voltage		$V_{GS}$	±12	V	
Continuous Drain Current, V <sub>GS</sub> @4.5	V.	I <sub>D</sub>	6.5	Α	
Pulsed Drain Current, V <sub>GS</sub> @4.5V	<sub>GS</sub> @4.5V I <sub>DM</sub>		30	Α	
Continuous Source Current (Diode C	Conduction) <sup>a,b</sup>	I <sub>S</sub>	1.4	Α	
Maximum Power Dissipation	Ta = 25°C	- P <sub>D</sub>	1.04	W	
	Ta = 75°C		0.625		
Operating Junction Temperature	on Temperature T <sub>J</sub> +150		+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

## **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	$R\Theta_{JF}$	83	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	120	°C/W

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board,  $t \le 5$  sec.





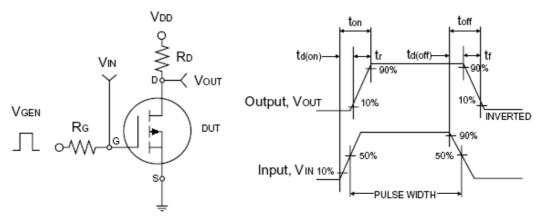
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**Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static	Static					
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.6	0.8	1.0	V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I <sub>GSS</sub>			±10	uA
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I <sub>D(ON)</sub>	30			Α
Drain Course On State Besistance	$V_{GS} = 4.5V, I_D = 6.5A$			15	22	mΩ
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 5.5A$	R <sub>DS(ON)</sub>	1	20	29	
Forward Transconductance	$V_{DS} = 10V, I_D = 6.5A$	9 <sub>fs</sub>		30		S
Diode Forward Voltage	$I_S = 1.7A, V_{GS} = 0V$	$V_{SD}$		0.6	1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	V 40V L C.TA	$Q_g$		15	20	
Gate-Source Charge	$V_{DS} = 10V, I_D = 6.5A,$ $V_{GS} = 4.5V$	$Q_gs$		3.4		nC
Gate-Drain Charge	V <sub>GS</sub> = 4.5 V	$Q_{gd}$		1.2		
Input Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$	$C_{iss}$		950		
Output Capacitance		C <sub>oss</sub>	1	450		рF
Reverse Transfer Capacitance	f = 1.0MHz	$C_{rss}$		135		
Switching <sup>c</sup>						
Turn-On Delay Time	V 40V D 400	t <sub>d(on)</sub>	-	140	200	
Turn-On Rise Time	$V_{DD} = 10V, R_L = 10\Omega,$ $I_D = 1A, V_{GEN} = 4.5V,$	t <sub>r</sub>	-	210	250	
Turn-Off Delay Time		t <sub>d(off)</sub>		3700	4800	nS
Turn-Off Fall Time	$R_{G} = 6\Omega$	t <sub>f</sub>		2000	2600	

#### Notes:

- a. pulse test: PW  $\leq 300 \mu S$ , duty cycle  $\leq 2\%$ b. For DESIGN AID ONLY, not subject to production testing. b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

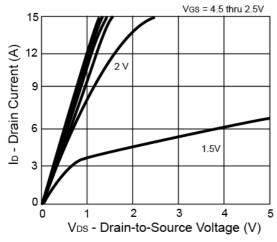


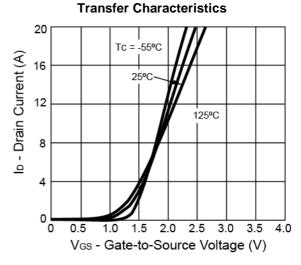


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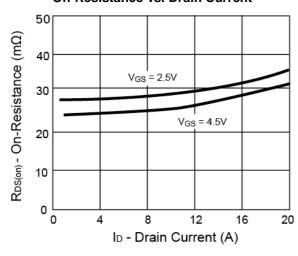
# Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



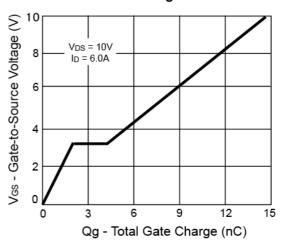




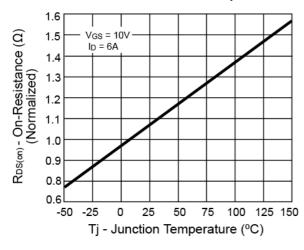
#### On-Resistance vs. Drain Current



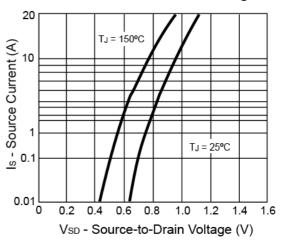
Gate Charge



## On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



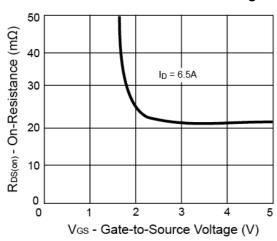


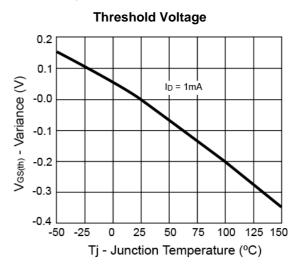


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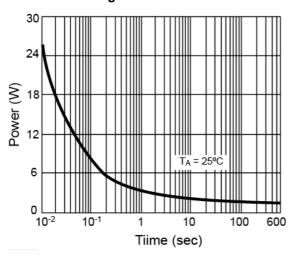
## **Electrical Characteristics Curve** (Ta = 25°C, unless otherwise noted)

#### **On-Resistance vs. Gate-Source Voltage**

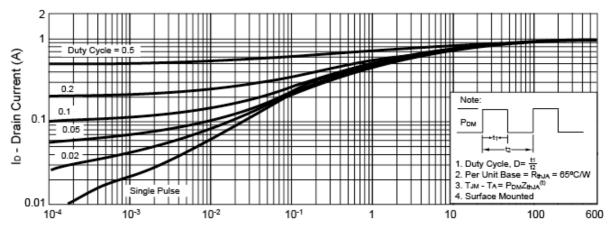




## Single Pulse Power



## Normalized Thermal Transient Impedance, Junction-to-Ambient



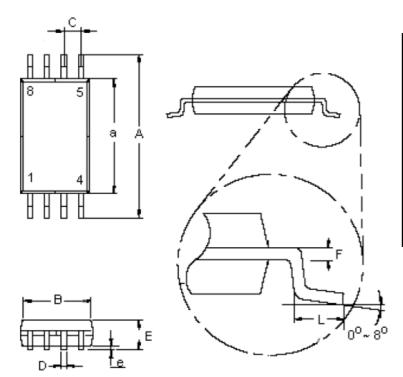
Square Wave Pulse Duration (sec)





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# **TSSOP-8 Mechanical Drawing**



TSSOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	6.20	6.60	0.244	0.260	
а	4.30	4.50	0.170	0.177	
В	2.90	3.10	0.114	0.122	
С	0.65 (typ)		0.025 (typ)		
D	0.25	0.30	0.010	0.019	
Е	1.05	1.20	0.041	0.049	
е	0.05	0.15	0.002	0.009	
F	0.127		0.005		
L	0.50	0.70	0.020	0.028	

# **Marking Diagram**



Y = Year Code

**M** = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



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